

2N6251

SILICON NPN TRIPLE DIFFUSED TYPE

DC-DC CONVERTER, SWITCHING REGULATOR
AND HIGH POWER AMPLIFIER APPLICATIONS.

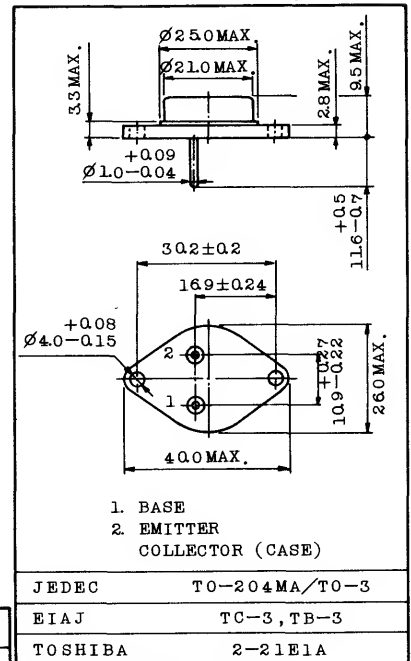
FEATURES:

- High Collector-Emitter Sustaining Voltage
: $V_{CEO(SUS)}=350V$ (Min.)
- Low Saturation Voltage : $V_{CE(sat)} < 1.5V$
@ $I_C=10A, I_B=1.67A$
- Excellent Switching Times : $t_r < 2.0\mu s, t_f < 1.0\mu s$
@ $I_C=10A, I_B=\pm 1.67A$
- High Collector Power Dissipation Capacity
: $P_C=175W$ (Max.)
- Excellent Area of Safe Operatings

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
*	Collector-Base Voltage	V_{CBO}	450	V	
	Collector-Emitter Sustaining Voltage ($R_{BE}=50\Omega$)	$V_{CER(SUS)}$	375	V	
*	Collector-Emitter Sustaining Voltage ($V_{BE}=0$)	$V_{CEX(SUS)}$	375	V	
	Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	350	V	
*	Emitter-Base Voltage	V_{EBO}	6	V	
*	Collector Current	DC	I_C	10	A
		Peak	I_{CM}	30	A
*	Base Current	I_B	10	A	
*	Collector Power Dissipation	$T_c=25^\circ C$	P_C	175	W
		$T_c=100^\circ C$		100	W
		Derate Linearly above $25^\circ C$		1.0	W/ $^\circ C$
*	Junction Temperature	T_j	200	$^\circ C$	
*	Storage Temperature Range	T_{stg}	-65 ~ 200	$^\circ C$	
*	Lead Temperature (0.8mm from case for 10s)	T_L	230	$^\circ C$	

Unit in mm



Weight : 15.8g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT		
* Collector Cut-off Current	ICEV	VCE=375V, VBE=-1.5V	-	-	5	mA		
* Collector Cut-off Current	ICEV	VCE=375V, VBE=-1.5V Tc=125°C	-	-	10	mA		
Collector Cut-off Current	ICEO	VCE=300V, IB=0	-	-	5	mA		
* Emitter Cut-off Current	IEBO	VEB=6V, IC=0	-	-	1	mA		
* Collector-Emitter Sustaining Voltage	V _{CER(SUS)} **	IC=0.2A, RBE=50Ω	375	-	-	V		
* Collector-Emitter Sustaining Voltage	V _{CEO(SUS)} **	IC=0.2A, IB=0	350	-	-	V		
* Emitter-Base Breakdown Voltage	V(BR)EBO	IE=1mA, IC=0	6	-	-	V		
* DC Current Gain	hFE	VCE=3V, IC=10A	6	-	50			
* Saturation Voltage	Collector-Emitter	VCE(sat)	IC=10A, IB=1.67A	-	-	1.5	V	
	Base-Emitter	VBE(sat)	IC=10A, IB=1.67A	-	-	2.25	V	
* Small Signal Current Gain	hfe	VCE=10V, IC=1A f=1MHz	2.5	-	-			
* Switching Time	Rise Time	tr			-	-	2.0	µs
	Storage Time	ts			-	-	3.5	µs
	Fall Time	tf			IB1=-IB2=1.67A DUTY CYCLE ≤ 2%	-	-	1.0
* Second Breakdown Collector Current (Base Forward Bias)	Is/b	VCE=30V, t=1s (non-repetitive)	5.8	-	-	A		
* Second Breakdown Energy (Base Reverse Bias)	Es/b	IC=10A, VBE=-4V L=50µH	2.5	-	-	mJ		

* In accordance with JEDEC registration data.

** The sustaining voltages VCER(SUS) and VCEO(SUS) MUST NOT be measured a curve tracer.

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